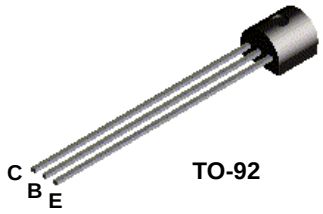
National Semiconductor™

Discrete POWER & Signal Technologies

MPS8050



NPN General Purpose Amplifier

This device is designed for general purpose audio amplifier applications at collector currents to 500 mA. Sourced from Process 30.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	25	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	1.0	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPS8050	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

NPN General Purpose Amplifier
(continued)

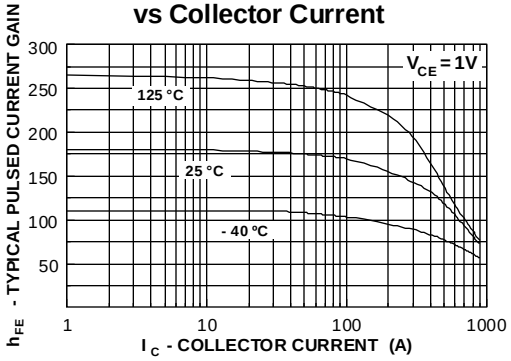
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	I_C = 30 mA, I_B = 0	25		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 100 µA, I_E = 0	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 100 µA, I_C = 0	6.0		V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 35 V, I_E = 0		0.1	µA
I_{CES}	Collector-Cutoff Current	V_{CE} = 20 V, I_E = 0		75	nA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 5.0 mA, V_{CE} = 1.0 I_C = 100 mA, V_{CE} = 1.0 I_C = 800 mA, V_{CE} = 1.0	45 80 40	 300 	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 800 mA, I_B = 80 mA		0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 800 mA, I_B = 80 mA		1.2	V

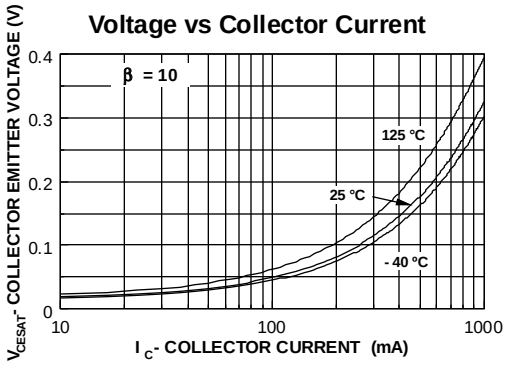
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 1.0%

Typical Characteristics

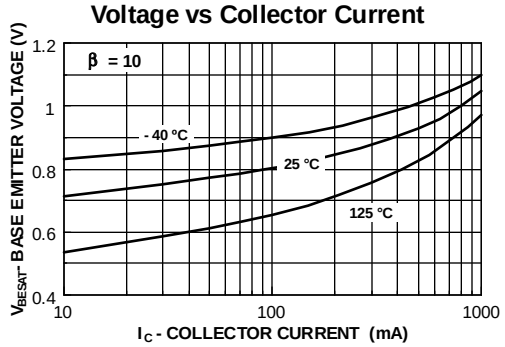
Typical Pulsed Current Gain vs Collector Current



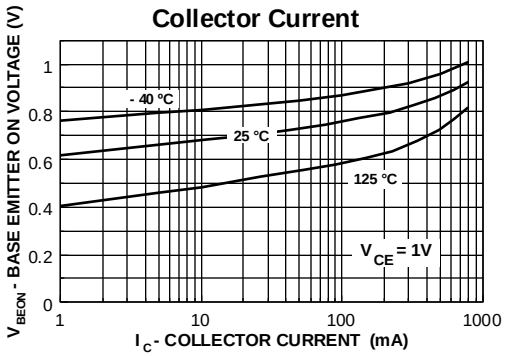
Collector-Emitter Saturation Voltage vs Collector Current



Base-Emitter Saturation Voltage vs Collector Current

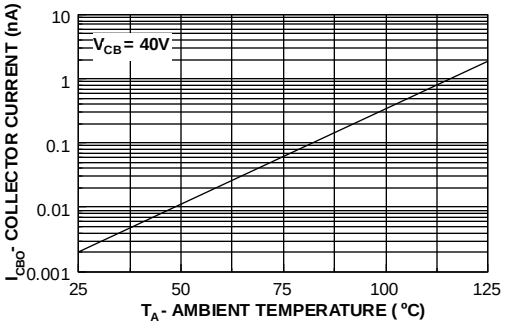


Base Emitter ON Voltage vs Collector Current

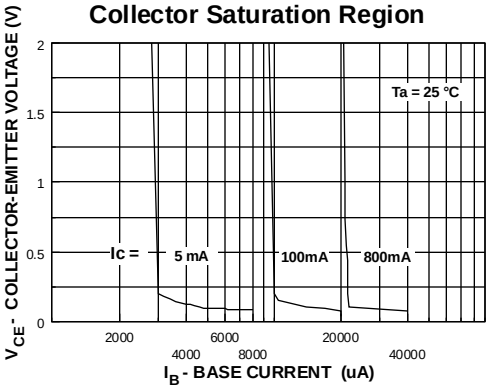


Typical Characteristics (continued)

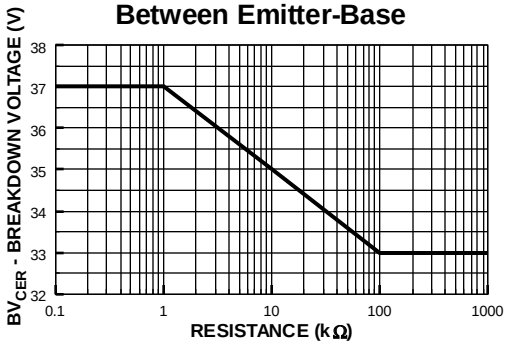
Collector-Cutoff Current vs. Ambient Temperature



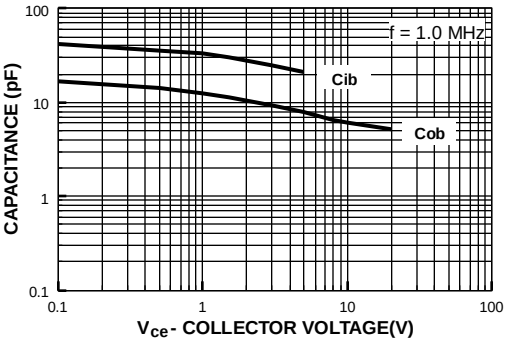
Collector Saturation Region



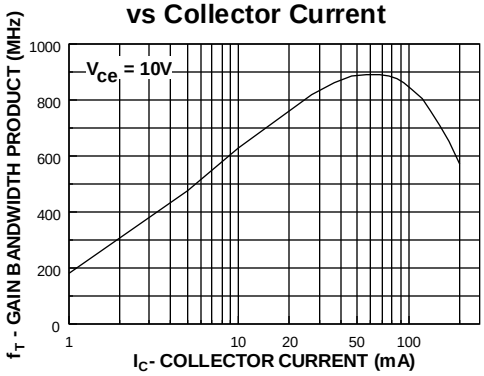
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Input and Output Capacitance vs Reverse Voltage



Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature